PTO/SB/17 (01-06)

Approved for use through 7/31/2006. OMB 0651-0032
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Ondering	A Reduction Act of					lete if Know		
FEE TRANSMITTAL						Patent#: 7,061,004		
						Issued: June 13, 2006		
For FY 2006					Kristy A. Campbell			
				Examiner Name	M	. C. Landau		
Applican	t claims small entity state	us. See 37 CFR 1.2	:7	Art Unit 2		2815		
TOTAL AMOU	NT OF PAYMENT	(\$) 100.00		Attorney Docket No. M4065.0		4065.0724/P	724 	
METHOD OF	PAYMENT (check	all that apply)					-	
Check x Credit Card Money Order None Other (please identify):								
Deposit Ac	count Deposit Account I	Number: <u>04-1073</u> ı	Deposit Acc	count Name:	Dic	kstein Shapiro	LLP	
For the	above-identified depo	sit account, the D	Director is	hereby authorize	ed to: (check	all that apply)		
Хc	harge fee(s) indicated	l below		Charg	e fee(s) indi	cated below, ex	cept for th	ne filing fee
C fe	harge any additional f e(s) under 37 CFR 1	ee(s) or underpay .16 and 1.17	ment of	x Credit	any overpay	ments		
FEE CALCU	_ATION (All the fe	es below are d	ue upo	n filing or may	be subjec	t to a surcha	rge.)	
1. BASIC FILIN	G, SEARCH, AND E							
	FII	LING FEES Small Entity	SE	ARCH FEES Small Entity	EXAMINA	ATION FEES Small Entity		
Application T	ype Fee (\$		Fee (\$		Fee (\$)	Fee (\$)	Fees F	Paid (\$)
Utility	300	150	500	250	200	100		
Design	200	100	100	50	130	65		
Plant	200	100	300	150	160	80		
Reissue	300	150	500	250	600	300		
Provisional	200	100	0	0	0	0		
2. EXCESS CL	AIM FEES							Small Entity
Fee Description	r 20 (including Reiss	uec)					Fee (\$) 50	Fee (\$) 25
	ent claim over 3 (incl	•					200	100
Multiple depend	·	aumg reessaus,					360	180
Total Claims	Extra Claims	Fee (\$)	Fee I	Paid (\$)	<u>Mul</u>	tiple Depende	nt Claims	
		· =			Fee	<u>(\$)</u>	ee Paid (\$	<u>)</u>
HP = highest num	ber of total claims paid for	, if greater than 20.						_
Indep. Claims	Extra Claims	Fee (\$)	Fee I	Paid (\$)				
HP = highest num	ber of independent claims	paid for, if greater that	an 3.					
3. APPLICATION SIZE FEE If the specification and drawings exceed 100 sheets of paper (excluding electronically filed sequence or computer listings under 37 CFR 1.52(e)), the application size fee due is \$250 (\$125 for small entity) for each additional 50 sheets or fraction thereof. See 35 U.S.C. 41(a)(1)(G) and 37 CFR 1.16(s).								
Total Sheet	<u>Extra Sheet</u>	s <u>Number</u>		dditional 50 or fra		Fee (\$)	Fee I	Paid (\$)
			(round up to a who	ole number) x	=	Foos	Paid (\$)	
4. OTHER FEE(S) Non-English Specification, \$130 fee (no small entity discount)								
Other (e.g., late filing surcharge): 1811/Certificate of correction 100.00								
SUBMITTED BY								
Signature	$\overline{\mathcal{L}}$	0/2	_	Registration No. (Attorney/Agent)	28,371	Telephone	(202) 42	 0-2232
Name (Drint/Tune)	Thomas I D'Amir			(Ministry Ball)	·	Date	August 7	2006

Certificate

AUG 1:0 2006

of Correction AUG 14 LUUD



Docket No.: M4065.0724/P724

(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Letters Patent of: Kristy A. Campbell

Patent No.: 7,061,004

Issued: June 13, 2006

For: RESISTANCE VARIABLE MEMORY

ELEMENTS AND METHODS OF

FORMATION

REQUEST FOR CERTIFICATE OF CORRECTION PURSUANT TO 37 CFR 1.322 & 1.323

Attention: Certificate of Correction Branch

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

Dear Sir:

Upon reviewing the above-identified patent, Patentee noted typographical errors which should be corrected.

In the U.S. Patent Documents portion of the References Cited section,

Applicant made the following error to be corrected. These 15 patents have "Lowery" listed as the inventor, which is a misspelling. They should have —Lowrey—as the inventor:

08/09/2006 HALIII 00000005 7861004

		01 FC:1811	100.00 OP	
6,404,665	6,501,111	6,511,867	6,545,907	
6,555,860	6,563,164	6,567,293	6,570,784	

Patent No.: 7,061,004 Docket No.: M4065.0724/P724

6,576,921	6,586,761	6,590,807	6,625,054
6,667,900	6,687,153	6,707,712	

In the Other Publications portion of the References Cited section, the PTO made the following error to be corrected:

"Titus, S.S.K.; Chatterj e, R.; Asokan, S., Electrical switching and short-range rder in As-T glasses, Phys. Rev. B 48 (1993) 14650-14652."

should read

--Titus, S.S.K.; Chatterjee, R.; Asokan, S., Electrical switching and short-range order in As-Te glasses, Phys. Rev. B 48 (1993) 14650-14652.--.

Also in Other Publications, Applicant made the following errors to be corrected:

"Kotkata, M.F.; Afif, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146."

should read

--Kotkata, M.F.; Afifi, M.A.; Labib, H.H.; Hegab, N.A.; Abdel-Aziz, M.M., Memory switching in amorphous GeSeTl chalcogenide semiconductor films, Thin Solid Films 240 (1994) 143-146.--;

"McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects o electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f."

should read

--McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987).--; and

"Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and exafs structural

Patent No.: 7,061,004 Docket No.: M4065.0724/P724

investigation, Transport-structure relations in fast ion and mixed conductors Proceedings of the 6th Riso International symposium, Sep. 9-13, 1985."

should read

--Tranchant, S.; Peytavin, S.; Ribes, M.; Flank, A.M.; Dexpert, H.; Lagarde, J.P., Silver chalcogenide glasses Ag-Ge-Se: Ionic conduction and EXAFS structural investigation, Transport-structure relations in fast ion and mixed conductors, Proc. of the 6th RISO Int'l Symp., Sep. 9-13, 1985.--.

In the Specification, Applicant made the following errors to be corrected:

Column 10, line 19, "include" should read --includes--;

Column 10, line 47, "via to the" should read --via the--;

Column 10, line 50, "to one additional" should read --to additional--; and

Column 11, line 1, "system" should read --systems--.

The errors were found in the application as filed by Applicant, and made by the PTO. Please charge our Credit Card in the amount of \$100.00 covering the fee set forth in 37 CFR 1.20(a). Credit Card Payment Form SB-2038, with a signature from an authorized cardholder, is enclosed.

The errors now sought to be corrected are inadvertent typographical errors the correction of which does not involve new matter or require reexamination.

Transmitted herewith is a proposed Certificate of Correction effecting such amendment. Patentee respectfully solicits the granting of the requested Certificate of Correction.

Patent No.: 7,061,004 Docket No.: M4065.0724/P724

The Director is hereby authorized to charge any deficiency in the fees filed, asserted to be filed or which should have been filed herewith (or with any paper hereafter filed in this application by this firm) to our Deposit Account No. 04-1073, under Order No. M4065.0724/P724.

Dated: August 7, 2006

Respectfully submitted,

Thomas J. D'Amico

Registration No.: 28,371

Elizabeth Parsons

Registration No.: 52,499 DICKSTEIN SHAPIRO LLP

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Attorneys for Applicant

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UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

Page _1_ of _2_

PATENT NO.

7,061,004

APPLICATION NO. :

10/622,482

ISSUE DATE

June 13, 2006

INVENTOR

Kristy A. Campbell

It is certified that errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the U.S. Patent Documents portion of the References Cited section, the following error is corrected for the inventor in the following 15 patents:

6,404,665	6,501,111	6,511,867	6,545,907
6,555,860	6,563,164	6,567,293	6,570,784
6,576,921	6,586,761	6,590,807	6,625,054
6,667,900	6,687,153	6,707,712	

[&]quot;Lowery" should read --Lowrey--.

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MAILING ADDRESS OF SENDER (Please do not use customer number below): Thomas J. D'Amico DICKSTEIN SHAPIRO LLP 1825 Eye Street, NW Washington, DC 20006-5403

"McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects o electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987)f."

should read

--McHardy et al., The dissolution of metals in amorphous chalcogenides and the effects of electron and ultraviolet radiation, 20 J. Phys. C.: Solid State Phys., pp. 4055-4075 (1987).--;

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Column 11, line 1, "system" should read --systems --.

MAILING ADDRESS OF SENDER (Please do not use customer number below): Thomas J. D'Amico **DICKSTEIN SHAPIRO LLP** 1825 Eye Street, NW Washington, DC 20006-5403

